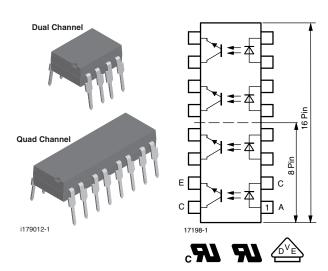


**Vishay Semiconductors** 

# **Optocoupler, Phototransistor Output, (Dual, Quad Channel)**



#### DESCRIPTION

The TCET2100/TCET4100 consists of a phototransistor optically coupled to a gallium arsenide infrared-emitting diode, available in 8 pin (dual channel) and 16 pin (quad channel) package.

#### FEATURES

- Extra low coupling capacity typical 0.2 pF
- High common mode rejection
- Low temperature coefficient of CTR
- Rated impulse voltage (transient overvoltage)
  V<sub>IOTM</sub> = 10 kV peak



RoHS

COMPLIANT

- Creepage current resistance according to VDE 0303/IEC 60112 comparative tracking index: CTI ≥ 175
- Thickness through insulation  $\ge 0.4$  mm
- Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC

#### AGENCY APPROVALS

- UL1577, file no. E52744 system code H, double protection
- CSA 22.2 bulletin 5A, double protection
- DIN EN 60747-5-5 (VDE 0884)
- FIMKO

ORDERING INFORMAT	2N				
ТС					
AGENCY CERTIFIED/PACKAG	CTR (%)				
UL, cUL, VDE	50 to 600				
DIP-8, dual channel	TCET2100				
DIP-16, quad channel	TCET4100				



### Vishay Semiconductors Optocoupler, Phototransistor Output, (Dual, Quad Channel)

PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
INPUT	· ·	•		
Reverse voltage		V <sub>R</sub>	6	V
Forward current		I <sub>F</sub>	60	mA
Forward surge current	t <sub>p</sub> ≤ 10 μs	I <sub>FSM</sub>	1.5	А
Power dissipation		P <sub>diss</sub>	100	mW
Junction temperature		Тj	125	°C
OUTPUT				
Collector emitter voltage		V <sub>CEO</sub>	70	V
Emitter collector voltage		V <sub>ECO</sub>	7	V
Collector current		Ι <sub>C</sub>	50	mA
Collector peak current	$t_p/T = 0.5, t_p \le 10 \text{ ms}$	I <sub>CM</sub>	100	mA
Power dissipation		P <sub>diss</sub>	150	mW
Junction temperature		Tj	125	°C
COUPLER	· ·	•		
Isolation test voltage (RMS)	t = 1 s	V <sub>ISO</sub>	5300	V <sub>RMS</sub>
Isolation voltage		V <sub>IORM</sub>	890	VP
Total power dissipation		P <sub>tot</sub>	250	mW
Operating ambient temperature range		T <sub>amb</sub>	- 55 to + 100	°C
Storage temperature range		T <sub>stg</sub>	- 55 to + 150	°C
Soldering temperature <sup>(2)</sup>	2 mm from case, t $\leq$ 10 s	T <sub>sld</sub>	260	°C

#### Notes

(1) Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute maximum ratings for extended periods of the time can adversely affect reliability.

<sup>(2)</sup> Refer to wave profile for soldering conditions for through hole devices.

<b>ELECTRICAL CHARACTERISTICS</b> (T <sub>amb</sub> = 25 °C, unless otherwise specified)								
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT		
INPUT								
Forward voltage	$I_F = \pm 50 \text{ mA}$	V <sub>F</sub>		1.25	1.6	V		
Junction capacitance	V <sub>R</sub> = 0 V, f = 1 MHz	Cj		50		pF		
OUTPUT								
Collector emitter voltage	I <sub>C</sub> = 1 mA	V <sub>CEO</sub>	70			V		
Emitter collector voltage	I <sub>E</sub> = 100 μA	V <sub>ECO</sub>	7			V		
Collector emitter cut-off current	$V_{CE} = 20 \text{ V}, I_F = 0, E = 0$	I <sub>CEO</sub>		10	100	nA		
COUPLER								
Collector emitter saturation voltage	I <sub>F</sub> = 10 mA, I <sub>C</sub> = 1 mA	V <sub>CEsat</sub>			0.3	V		
Cut-off frequency	$V_{CE} = 5 \text{ V}, \text{ I}_{\text{F}} = 10 \text{ mA}, \\ \text{R}_{\text{L}} = 100 \ \Omega$	f <sub>c</sub>		110		kHz		
Coupling capacitance	f = 1 MHz	Ck		0.3		pF		

Note

• Minimum and maximum values were tested requierements. Typical values are characteristics of the device and are the result of engineering evaluations. Typical values are for information only and are not part of the testing requirements.

CURRENT TRANSFER RATIO							
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT	
I <sub>C</sub> /I <sub>F</sub>	$V_{CE} = 5 \text{ V}, \text{ I}_{F} = 5 \text{ mA}$	CTR	50		600	%	



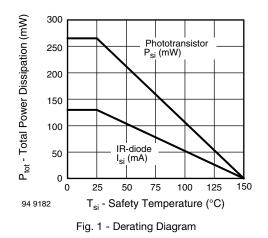
### Optocoupler, Phototransistor Output, Vishay Semiconductors (Dual, Quad Channel)

MAXIMUM SAFETY RATINGS								
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT		
INPUT								
Forward current		IF			275	mA		
OUTPUT								
Power dissipation		P <sub>diss</sub>			400	mW		
COUPLER								
Rated impulse voltage		V <sub>IOTM</sub>			10	kV		
Safety temperature		T <sub>si</sub>			175	°C		

Note

• According to DIN EN 60747-5-5 (see figure 2). This optocoupler is suitable for safe electrical isolation only within the safety ratings. Compliance with the safety ratings shall be ensured by means of suitable protective circuits.

INSULATION RATED PARAMETERS							
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT	
Partial discharge test voltage - routine test	100 %, t <sub>test</sub> = 1 s	V <sub>pd</sub>	1.669			kV	
Partial discharge test voltage - lot test (sample test)	$t_{Tr} = 60 \text{ s}, t_{test} = 10 \text{ s},$ (see figure 2)	VIOTM	10			kV	
		V <sub>pd</sub>	1.424			kV	
Insulation resistance	V <sub>IO</sub> = 500 V	R <sub>IO</sub>	10 <sup>12</sup>			Ω	
	$V_{IO} = 500 \text{ V}, \text{ T}_{amb} = 100 ^{\circ}\text{C}$	R <sub>IO</sub>	10 <sup>11</sup>			Ω	
	$V_{IO} = 500 \text{ V}, \text{ T}_{amb} = 150 \text{ °C}$ (construction test only)	R <sub>IO</sub>	10 <sup>9</sup>			Ω	



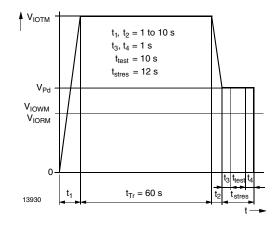
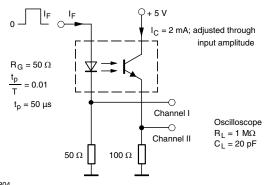


Fig. 2 - Test Pulse Diagram for Sample Test According to DIN EN 60747-5-5/DIN EN 60747-; IEC60747

### Vishay Semiconductors Optocoupler, Phototransistor Output, (Dual, Quad Channel)

SWITCHING CHARACTERISTICS							
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT	
Delay time	$\label{eq:VS} \begin{array}{l} V_{S} = 5 \; V, \; I_{C} = 2 \; mA, \; R_{L} = 100 \; \Omega, \\ (\text{see figure 3}) \end{array}$	t <sub>d</sub>		3		μs	
Rise time	$\label{eq:VS} \begin{array}{l} V_{S} = 5 \; V, \; I_{C} = 2 \; mA, \; R_{L} = 100 \; \Omega, \\ (\text{see figure 3}) \end{array}$	t <sub>r</sub>		3		μs	
Turn-on time	$\label{eq:VS} \begin{array}{l} V_{S} = 5 \; V, \; I_{C} = 2 \; mA, \; R_{L} = 100 \; \Omega, \\ (\text{see figure 3}) \end{array}$	t <sub>on</sub>		6		μs	
Storage time	$\label{eq:VS} \begin{array}{l} V_{S} = 5 \; V, \; I_{C} = 2 \; mA, \; R_{L} = 100 \; \Omega, \\ (\text{see figure 3}) \end{array}$	t <sub>s</sub>		0.3		μs	
Fall time	$\label{eq:VS} \begin{array}{l} V_{S} = 5 \; V, \; I_{C} = 2 \; mA, \; R_{L} = 100 \; \Omega, \\ (\text{see figure 3}) \end{array}$	t <sub>f</sub>		4.7		μs	
Turn-off time	$\label{eq:VS} \begin{array}{l} V_{S} = 5 \; V, \; I_{C} = 2 \; mA, \; R_{L} = 100 \; \Omega, \\ (\text{see figure 3}) \end{array}$	t <sub>off</sub>		5		μs	
Turn-on time	$V_S = 5 \text{ V}, I_F = 10 \text{ mA}, R_L = 1 \text{ k}\Omega,$ (see figure 4)	t <sub>on</sub>		9		μs	
Turn-off time	$\label{eq:VS} \begin{array}{l} V_S = 5 \text{ V}, \text{ I}_F = 10 \text{ mA}, \text{ R}_L = 1 \text{ k}\Omega, \\ (\text{see figure 4}) \end{array}$	t <sub>off</sub>		10		μs	



95 10804

Fig. 3 - Test Circuit, Non-Saturated Operation

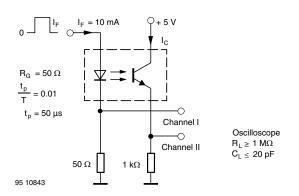


Fig. 4 - Test Circuit, Saturated Operation

 $\mathsf{I}_\mathsf{F}$ 0 t p  $I_{C}$ 100 % 90 % 10 % 0 t  $t_{\rm f}$ t<sub>off</sub> Pulse duration Delay time  $egin{aligned} t_p \ t_d \ t_r \ t_{on} \ (= t_d + t_r) \end{aligned}$ Storage time Fall time t Turn-off time Rise time  $(= t_s + t_f)$ t<sub>off</sub> Turn-on time 96 11698







### Optocoupler, Phototransistor Output, Vishay Semiconductors (Dual, Quad Channel)

### TYPICAL CHARACTERISTICS (T<sub>amb</sub> = 25 °C, unless otherwise specified)

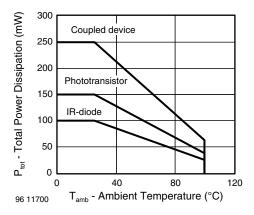


Fig. 6 - Total Power Dissipation vs. Ambient Temperature

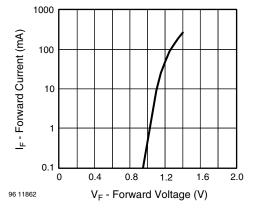


Fig. 7 - Forward Current vs. Forward Voltage

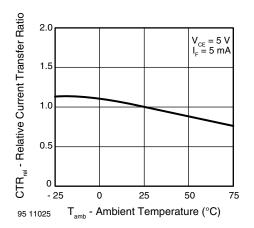


Fig. 8 - Relative Current Transfer Ratio vs. Ambient Temperature

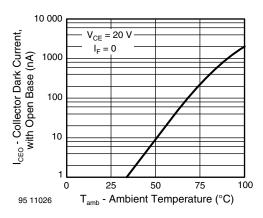


Fig. 9 - Collector Dark Current vs. Ambient Temperature

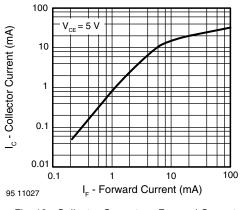


Fig. 10 - Collector Current vs. Forward Current

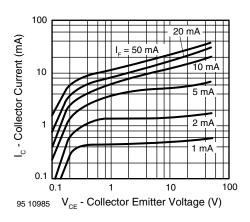


Fig. 11 - Collector Current vs. Collector Emitter Voltage

### Vishay Semiconductors Optocoupler, Phototransistor Output, (Dual, Quad Channel)



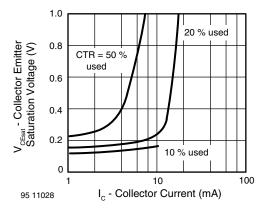


Fig. 12 - Collector Emitter Saturation Voltage vs. Collector Current

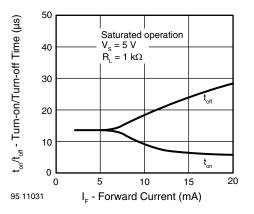


Fig. 15 - Turn-on/off Time vs. Forward Current

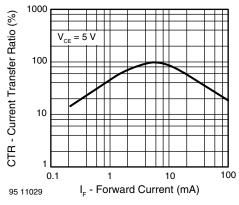


Fig. 13 - Current Transfer Ratio vs. Forward Current

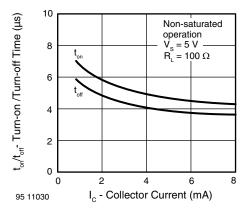


Fig. 14 - Turn-on/off Time vs. Collector Current

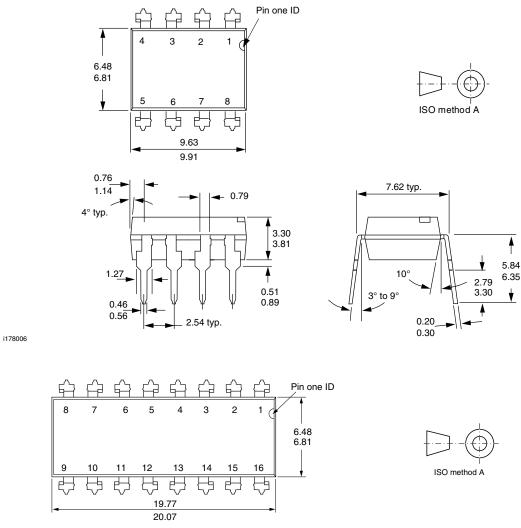


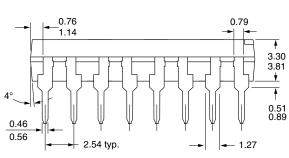
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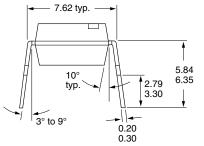
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Optocoupler, Phototransistor Output, Vishay Semiconductors (Dual, Quad Channel)

#### **PACKAGE DIMENSIONS** in millimeters

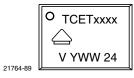






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#### **PACKAGE MARKING**





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